



### **UPA2815T1S-E2-AT Information**

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Part Number UPA2815T1S-E2-AT

ManufacturerRenesas Electronics AmericaCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 30V 21A 8HWSON

Package 8-PowerWDFN

For the pricing/inventory/lead time, please contact

us

For Reference Only

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## **UPA2815T1S-E2-AT Specifications**

Manufacturer Part Number         UPA2815TIS-E2-AT           Manufacturer         Renesas Electronics America           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-PowerWDFN           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         21A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         47nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1760pF @ 10V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.5W (Ta)           Rds On (Max) @ Id, Vgs         11 mOhm @ 21A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-HWSON (3.3x3.3)           Package / Case         8-PowerWDFN		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage8-PowerWDFNSeries-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C21A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs47nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1760pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta)Rds On (Max) @ Id, Vgs11 mOhm @ 21A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-HWSON (3.3x3.3)Package / Case8-PowerWDFN	Manufacturer Part Number	UPA2815T1S-E2-AT
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Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  21A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **E20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 21A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  8-HWSON (3.3x3.3)  Package / Case  **Case  **Case  **INSON (Max) (M	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  21A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 21A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  8-HWSON (3.3x3.3)  Package / Case	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 21A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 47nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 1760pF @ 10V  Vgs (Max) ±20V  FET Feature - Power Dissipation (Max) 1.5W (Ta)  Rds On (Max) @ Id, Vgs 11 mOhm @ 21A, 10V  Operating Temperature 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package 8-HWSON (3.3x3.3)  Package / Case 8-PowerWDFN	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 21A, 10V  Deprating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Power WDFN	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 47nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1760pF @ 10V Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 21A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-HWSON (3.3x3.3) Package / Case 8-PowerWDFN	Current - Continuous Drain (Id) @ 25°C	21A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1760pF @ 10V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 21A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-HWSON (3.3x3.3)  Package / Case  8-PowerWDFN	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 21A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-HWSON (3.3x3.3)  Package / Case  8-PowerWDFN	Vgs(th) (Max) @ Id	-
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta)Rds On (Max) @ Id, Vgs11 mOhm @ 21A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-HWSON (3.3x3.3)Package / Case8-PowerWDFN	Gate Charge (Qg) (Max) @ Vgs	47nC @ 10V
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Rds On (Max) @ Id, Vgs11 mOhm @ 21A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-HWSON (3.3x3.3)Package / Case8-PowerWDFN	FET Feature	-
Operating Temperature 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package 8-HWSON (3.3x3.3)  Package / Case 8-PowerWDFN	Power Dissipation (Max)	1.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-HWSON (3.3x3.3) Package / Case 8-PowerWDFN	Rds On (Max) @ Id, Vgs	11 mOhm @ 21A, 10V
Supplier Device Package 8-HWSON (3.3x3.3) Package / Case 8-PowerWDFN	Operating Temperature	150°C (TJ)
Package / Case 8-PowerWDFN	Mounting Type	Surface Mount
	Supplier Device Package	8-HWSON (3.3x3.3)
Report errors?	Package / Case	8-PowerWDFN
•		Report errors?

#### **UPA2815T1S-E2-AT Guarantees**



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **UPA2815T1S-E2-AT Payment Methods**



















## **UPA2815T1S-E2-AT Shipping Methods**













If you have any question about UPA2815T1S-E2-AT, please do not hesitate to contact us!

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